



## PRODUCT DATA SHEET



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**Datasheet**



**Resources**



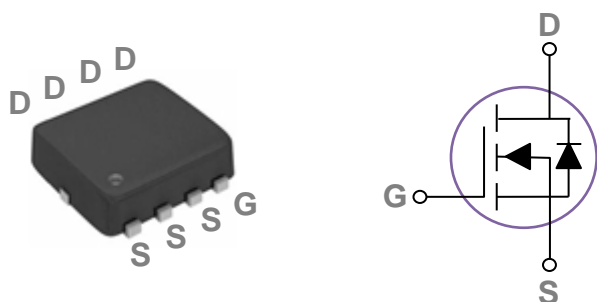
**Samples**

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.jg-semi.cn](http://www.jg-semi.cn). Please email any questions regarding the system integration to [JINGAO\\_questions@jgsemi.com](mailto:JINGAO_questions@jgsemi.com).

## General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

## PPAK3X3 Pin Configuration



BVDSS	RDS(ON)	ID
30V	4.5mΩ	64A

## Features

- 30V, 64A,  $R_{DS(ON)} = 4.5m\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

## Applications

- Networking
- Load Switch
- LED applications

## Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	64	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	40	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	256	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	115	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	48	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	44.6	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.36	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.8	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	---	3.6	4.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	4.9	6.4	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.17	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	---	10	---	S

**Dynamic and switching Characteristics**

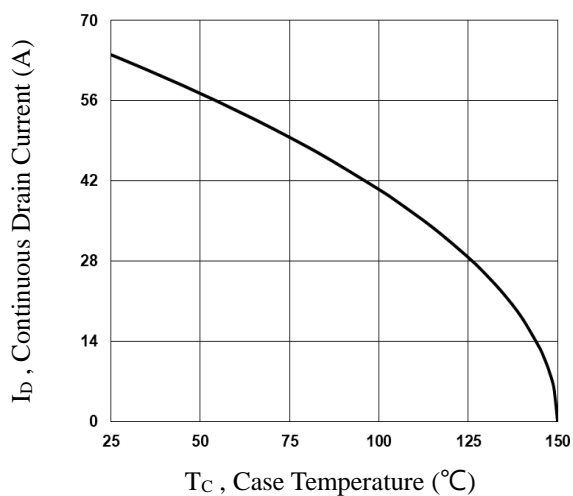
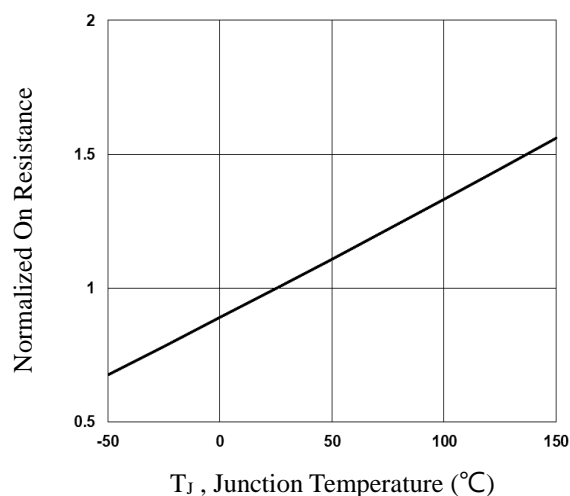
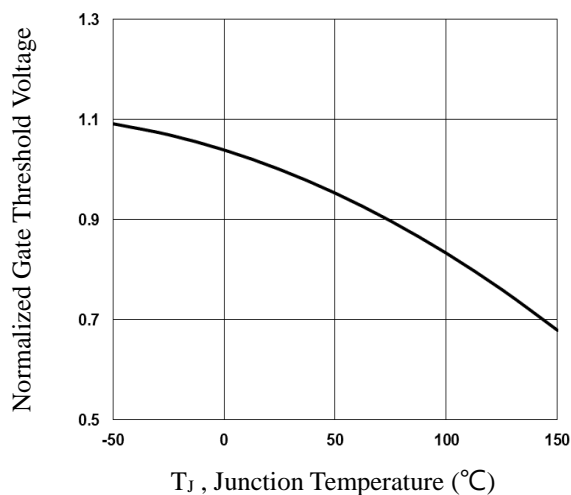
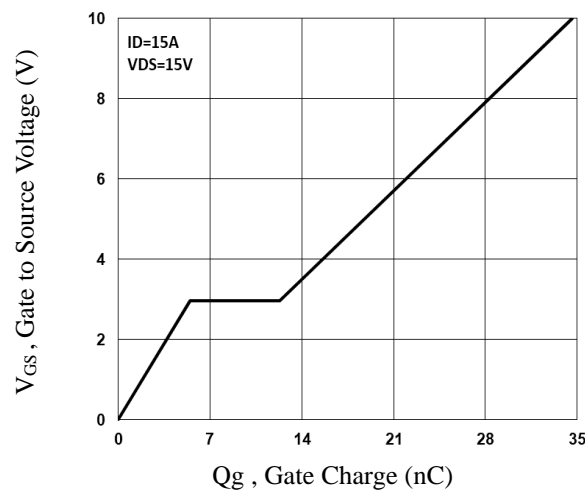
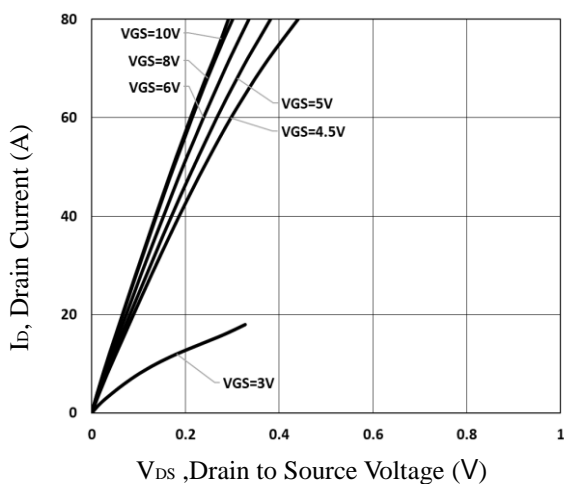
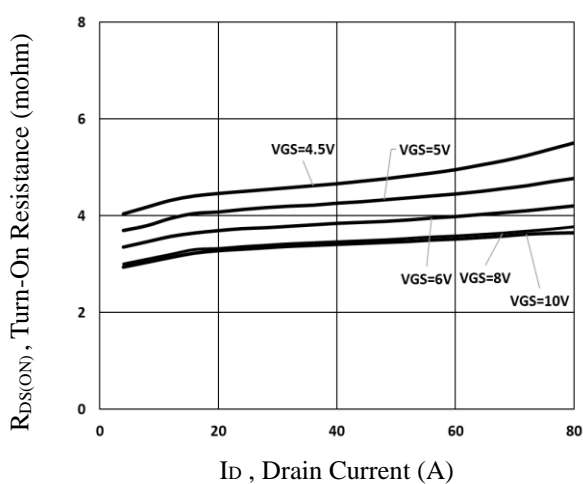
Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =15A	---	34.6	70	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	5.5	11	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	6.8	13	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A	---	9.7	20	ns
T <sub>r</sub>	Rise Time <sup>3, 4</sup>		---	15.8	31	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	37.4	75	
T <sub>f</sub>	Fall Time <sup>3, 4</sup>		---	12	24	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1MHz	---	1910	3800	pF
C <sub>oss</sub>	Output Capacitance		---	300	600	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	230	460	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	1.14	---	Ω

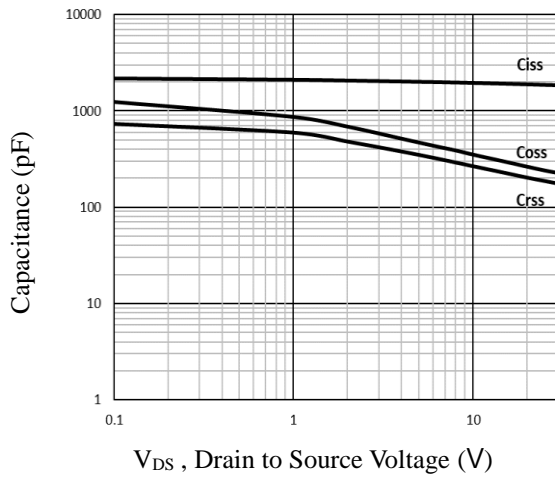
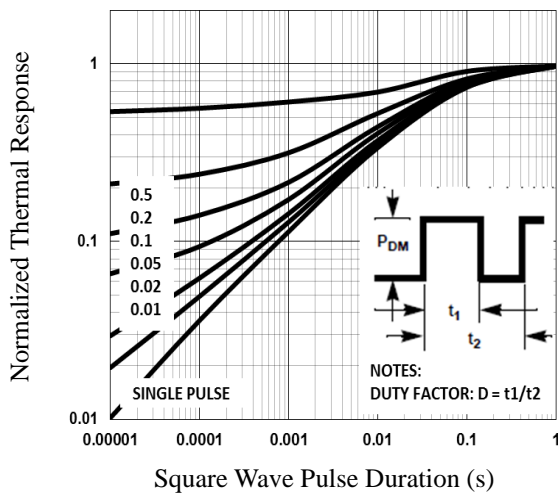
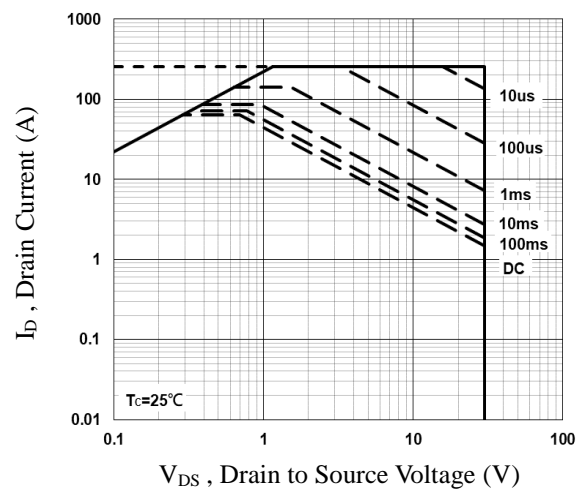
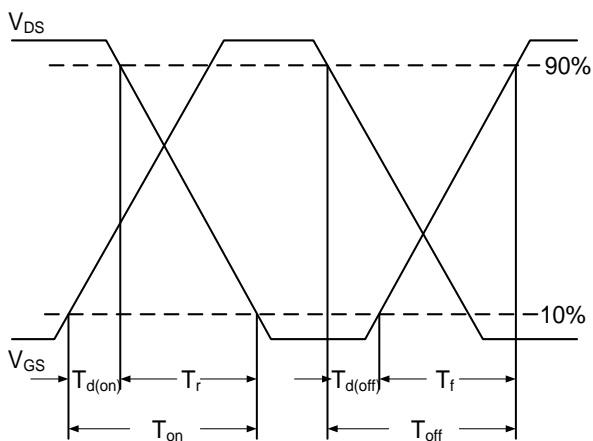
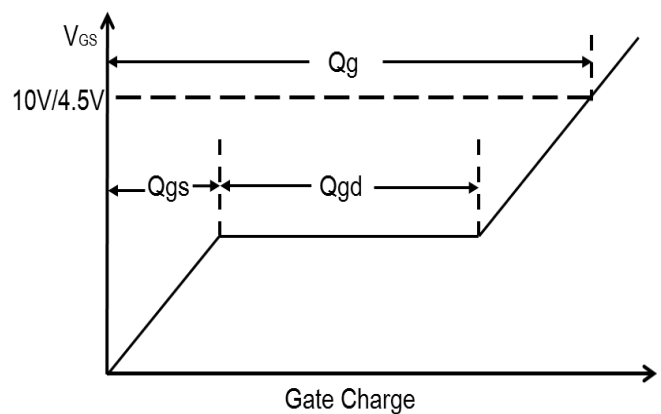
**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	64	A
I <sub>SM</sub>	Pulsed Source Current		---	---	128	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

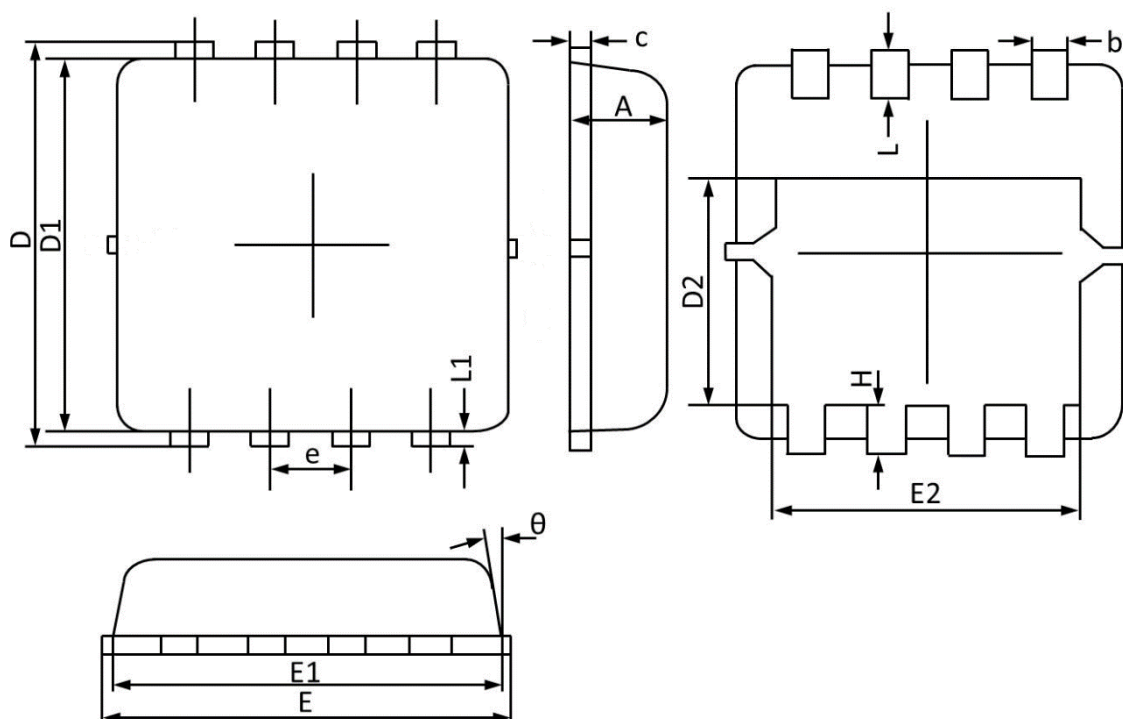
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=48A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
4. Essentially independent of operating temperature.


**Fig.1 Continuous Drain Current vs. TC**

**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$** 

**Fig.3 Normalized  $V_{th}$  vs.  $T_J$** 

**Fig.4 Gate Charge Characteristics**

**Fig.5 Typical Output Characteristics**

**Fig.6 Turn-On Resistance vs.  $I_D$**

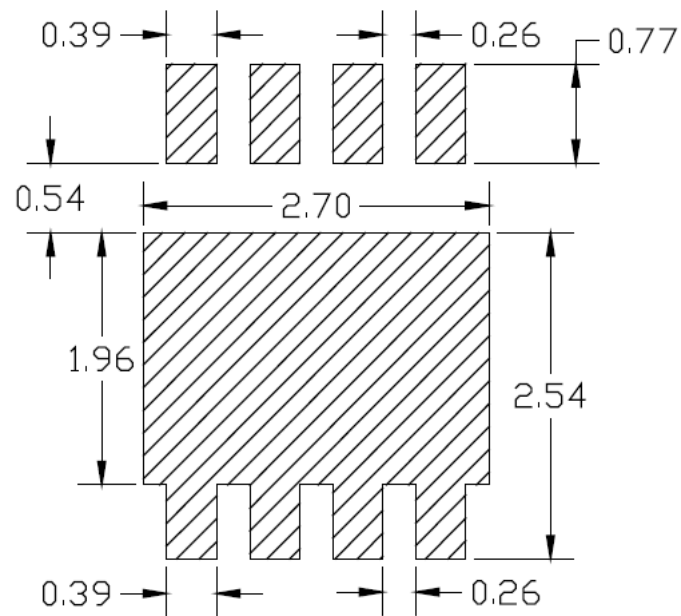

**Fig.7 Capacitance Characteristics**

**Fig.8 Normalized Transient Impedance**

**Fig.9 Maximum Safe Operation Area**

**Fig.10 Switching Time Waveform**

**Fig.11 Gate Charge Waveform**

## PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.250	0.014	0.010
c	0.250	0.100	0.010	0.004
D	3.500	3.050	0.138	0.120
D1	3.200	2.900	0.126	0.114
D2	1.950	1.350	0.077	0.053
E	3.400	3.000	0.134	0.118
E1	3.300	2.900	0.130	0.114
E2	2.600	2.350	0.102	0.093
e	0.65BSC		0.026BSC	
H	0.750	0.300	0.030	0.012
L	0.600	0.300	0.024	0.012
L1	0.200	0.060	0.008	0.002
θ	14°	6°	14°	6°

## PPAK3X3 RECOMMENDED LAND PATTERN



unit : mm

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